Form PTO (Rev. 2-32)		U.S. Department of Commerce Patent and Trademark Office			IMPJ-0	Atty. Docket No. IMPJ-0004		Serial No. 10/681,577		
O I P Sinformation Disclosure Statement by Applicant					Applicant: Diorio et al.					
(Use several sheets if necessary)					Filed:	Filed: 10/7/03 Group: Unknown				
2 0 200				U.S. Patent Docui	nents					
Miberapid	<del>9/-</del>	Document No.	Date	Name		Class	Subclass	Filing	Date	
111	A	4,763,105	08/09/88	Jeng		340	347	07/08/	87	
THE	В	4,962,380	10/09/90	Meadows		341	120	09/21/	89	
	C	4,968,988	11/06/0	Miki et al.		341	141	11/22/	88	
++	D	5,270,963	12/14/93	Allen et al.		364	861	07/06/	90	
+	E	5,627,392	05/06/97	Diorio et al.		257	315	03/07/	95	
	F	5,825,063	10/20/98	Diorio et al.		257	316	07/26/	96	
+ +	G	5,875,126	02/23/99	Minch et al.		365	185.01	09/26/	96	
_	Н	5,898,613	04/27/99	Diorio et al.		365	185.03	06/25/97		
-+	I	5,914,84	06/22/99	Diorio et al.		365	185.03	06/01/9	98	
	J	5,986,927	11/16/99	Minch et al.		365	185.01	11/10/	98	
	K	5,990,512	11/23/99	Diorio et al.		257	314	04/22/	97	
<del>-}</del>	L	6,125,053	09/26/00	Diorio et al.		365	185.03	11/30/	98	
	M	6,144,581	11/07/00	Diorio et al.		365	185.03	11/30/	98	
1	N	6,664,909	12/16/03	Hyde et al.		341	144	08/13/0	01	
			<del> </del>				•			
				Foreign Docume	ents					
T14		Danimant Na	Data	Country		Class	Subclass	Translatio		
Init.		Document No.	Date	Country		Class	Subclass	res	NO	
		·		<u> </u>		<del> </del>				
				<u> </u>	<del></del>	<del> </del>			-	
				<del> </del>		-			<del> </del>	
<u>.</u>	/			)	. D.4. D		. 1	<u></u>		
11.1	0	Other Doc Diorio et al., "Ada		ding Author, Title				2002.		
MIN		Proceedings of the	IEEE, Vol. 90.	, No. 3, p. 345-357	•					
HU)	P	Figueroa et al., "A 2001, Nonvolatile	Floating-Gate Semiconductor	Trimmable High-R Memory Worksho	esolution Da p, Monterey	, CA, pp. 46	-47.			
HIN	Q	Hyde et al., "A Flo CMOS", 2002, Syr					Converter in S	tandard 0.25	μm ——	
		140-1	0/02/2	(E) /		Date Cons	sidered /	2/00	701	
Examiner									,,,,	

Form PTO 1449 (Rev. 2-32) U.S. Department of Commerce Patent and Trademark Office  Information Disclosure Statement by Applicant						Atty. Docket No. Serial No.: 10/681,577					
						Applicant: Christopher J. Diorio et al.					
(Use several sheets if necessary)						Filed: September 7, 2003 Group: 2816					
								•			
Init.			Document No.	Date	U.S. Patent Docu Name	ments	Class	Subclass	Filing	Date Date	
141	A	$\overline{}$	2001/0020861	9/13/2001	Hirose				3/6/2		
10,1	E	_	2001/0054920	12/27/2001	Tsujino		<del></del>			/2000	
HIN.	<del>  </del>		5,952,891	9/14/1999	Boudry				6/13/		
.		-			<u> </u>						
			_						+		
							ļ <u>.                                    </u>				
		_	<u></u>			<del></del>	ļ				
		_									
		$\dashv$					· · ·				
· · · · ·		1			Foreign Docum	onte	I				
					Poreign Docum	icitis			Tr	anslation	
Init.			Document No.	Date	Country		Class	Subclass	Yes	No	
	_										
- 7	_				uding Author, Tit					<u>-</u>	
HER	4	D	Systems, August 8	-11, 2000, pp. 10	048-1051.					uits and	
HIN)	/	E	International Searc	ch Report for app	olication PCT/US (	03/31792, dat	e mailed A	ugust 12, 2004.	•		
									•		
	$\dashv$										
		•									
Examin	ner		HAI L.	NOU	VON		Date Cor	nsidered 12	10210	4	
Evamin	ner:	Init	ial if citation conside	rad whather or	not citation is in s	onformance v	ith MDED	600: Draw line	through of	tation if	

not in conformance and not considered. Include a copy of this form with the next communication to applicant.

				CIPE				Page	e <u>1</u> of 1
Form PTC (Rev. 2-3)	2)	U.S. Department of	k Office	JUN 0 7 2004 2	Atty. Docket No. IMPJ-0004		Serial No. 10/681,577		
	Info	rmation Disclosure St	pplicant, white	Applicant: Christopher J. Diorio et al. Filed: Group:					
	Information Disclosure Statement by Applicant, to the (Use several sheets if necessary)					7, 2003	Group: 2816		
			1	J.S. Patent Documen	.tc				
Init.		Document No.	Date	Name	165	Class	Subclass	Filing	Date
JH D	A	4,783,783	11/08/1988	Nagai et al.			<u> </u>		
1	В	4,935,702	06/19/1990	Mead et al.				·	
	С	5,933,039	08/03/1999	Hui et al.					
	D	5,939,945	08/17/1999	Thewes et al.					
1.	E	6,134,182	10/17/2000	Pilo et al.					
1	F	6,320,788	11/20/2001	Sansbury et al.					
								<u> </u>	
								<u> </u>	
								<u> </u>	
								ļ	
							_	_	
								<u> </u>	
			<u> </u>				<u> </u>		·
				Foreign Documents					
			···	Poreign Documents		<u>.                                      </u>		Tran	slation
Init.	/	Document No.	Date	Country		Class	Subclass	Yes	No
ALN	G	0 298 618 A	01/11/1989	EP				ļ	ļ
		<u> </u>							<u></u>
	,	Other Docu	ments (Inclu	ling Author, Title, D	ate, Perti	nent Pages, o	etc.)		
HIN,	Н	Partial International Search for International Application No. PCT/US03/31792, date mailed April 2, 2004.							
HEN	I	Carley, L. Richard, "Trimming Analog Circuits Using Floating-Gate Analog MOS Memory", IEEE Journal of Solid-State Circuits, Vol. 24, No. 6, pp. 1569-1575, December 1989.							
T.		L	. 10			D-4- C	11		-
Examiner		HAI L.1				Date Consid	12/0		4
		al if citation considered							ation
II HOL III CO	MIOLI	nance and not consider	tu. miciude a (	soby or any torm win	THE BEXT C	CHRITMITCHIC	n to applicant.		